

ON THE ELECTRON
HALL MOBILITY TEMPERATURE
MINIMA IN IRRADIATED SILICON

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S u m m a r y

The Hall mobility of electrons μ_H in P-doped silicon single crystals is measured in the temperature range $T = 77 \div 300$ K in series of samples both before and after irradiation with electrons or protons and thermal treatment. In the low-temperature region, the magnitude of μ_H significantly decreases with radiation dose. In some cases, one or two minima on the curves $\mu_H(T)$ have been detected. The explanation is given by using the model on the thermal polarization of the pairs of defects produced by irradiation.